SiC Schottky Barrier Diode

V_R	1200V		
I _F	15A ^{*1}		
Q_{C}	51nC		

Features

- 1) Shorter recovery time
- 2) Reduced temperature dependence
- 3) High-speed switching possible

(C) Cathode

●Inner Circuit

Construction

Silicon carbide epitaxial planar type Schottky diode

● Absolute Maximum Ratings (T_i = 25°C)

Parameter		Symbol	Value	Unit
Reverse voltage (re	epetitive peak)	V_{RM}	1200	V
Reverse voltage (D	verse voltage (DC) V _R 1200		1200	V
Continuous forward	l current	I _F	15	
Surge non- repetitive forward current	PW=10ms sinusoidal, T _j =25°C		62	А
	PW=10ms sinusoidal, T _j =150°C	$I_{FSM}^{}^{*2}}$	46	А
	PW=10μs square, T _j =25°C		240	А
i ² t value	1≦PW≦10ms, T _j =25°C	$\int i^2 dt^2$	19	A ² s
	1≦PW≦10ms, T _j =150°C	J i ⁻ dt	10	A ² s
Junction temperatu	re	T _j	Γ _j 175	
Range of storage to	e of storage temperature T,		-55 to +175	°C

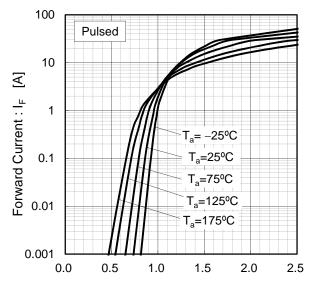
^{*1} Limited by T_i *2 Assumes $Z_{th(i-a)}$ of 0.50 °C/W or less. (Pulse Width = 8.3ms)

•Electrical characteristics $(T_j = 25^{\circ}C)$

Parameter	Symbol	Conditions	Values			l loit
			Min.	Тур.	Max.	Unit
DC blocking voltage	V_{DC}	$I_R = 0.3 \text{mA}$	1200	-	-	V
Forward voltage	V _F	I _F =15A,T _j =25°C	-	1.4	1.6	V
		I _F =15A,T _j =150°C	-	1.8	-	V
		I _F =15A,T _j =175°C	-	1.9	-	V
Reverse current	I _R	V _R =1200V,T _j =25°C	-	15	300	μΑ
		V _R =1200V,T _j =150°C	-	120	-	μΑ
		V _R =1200V,T _j =175°C	-	195	-	μΑ
Total capacitance	С	V _R =1V,f=1MHz	-	800	-	pF
		V _R =800V,f=1MHz	-	60	-	pF
Total capacitive charge	Q_{C}	V _R =800V,di/dt=500A/μs	-	51	-	nC
Switching time	t _C	V _R =800V,di/dt=500A/μs	-	18	-	ns

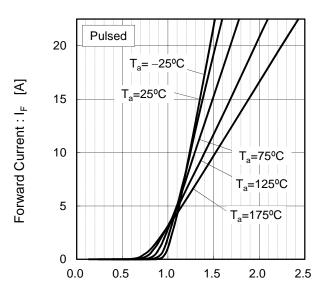
•Electrical characteristic curves

Fig.1 V_F - I_F Characteristics



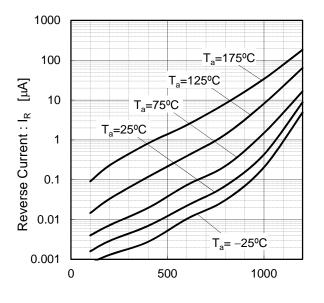
Forward Voltage : V_F [V]

Fig.2 V_F - I_F Characteristics



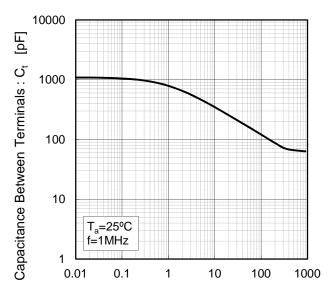
Forward Voltage : V_F [V]

Fig.3 V_R - I_R Characteristics



Reverse Voltage : V_R [V]

Fig.4 V_R-C_t Characteristics

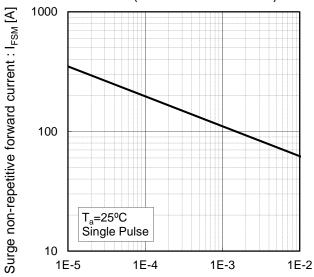


Reverse Voltage : V_R [V]

Forward Current: IF

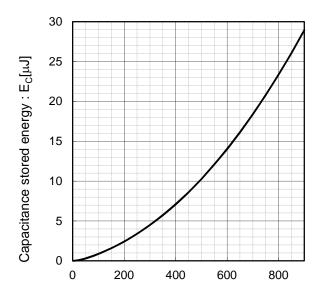
•Electrical characteristic curves

Fig.5 Surge non-repetitive forward current vs. Pulse width (Sinusoidal waveform)



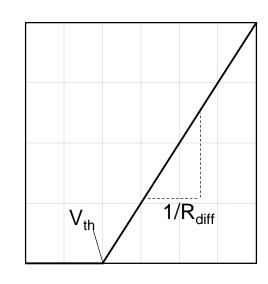
Pulse Width: PW [s]

Fig.6 Typical capacitance store energy



Reverse Voltage : V_R [V]

Fig.7 Equivalent forward current curve



Forward Voltage: V_F

$$V_F = V_{th} + R_{diff} I_F$$

$$V_{th} (T_j) = a_0 + a_1 T_j$$

 $R_{diff} (T_j) = b_0 + b_1 T_j + b_2 T_j^2$

Symbol	Typical Value	Unit
a_0	9.93E-01	V
a ₁	-1.27E-03	V/°C
b_0	2.43E-02	Ω
b ₁	1.37E-04	Ω/°C
b ₂	8.87E-07	Ω /°C ²

 T_i in °C; -55 °C < T_i < °C; I_F < 30A

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